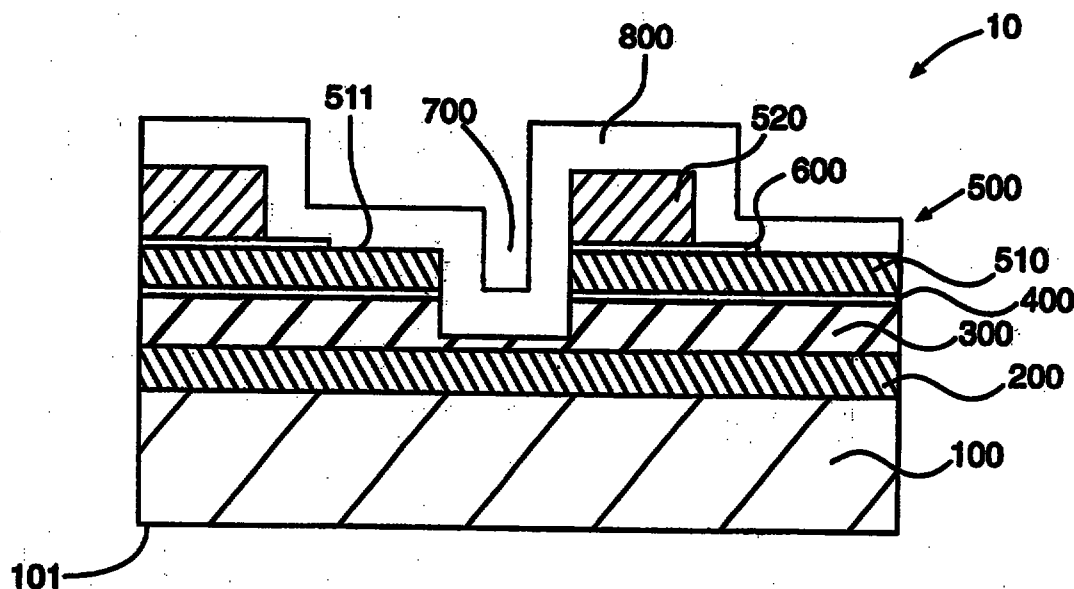




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(54) Title: **AN ELECTRODE STRUCTURE FOR HIGH RESOLUTION ORGANIC LIGHT-EMITTING DIODE DISPLAYS AND METHOD FOR MAKING THE SAME**



(57) Abstract

The invention is directed to an electrode structure (500) for an organic light-emitting device display (10). The electrode structure includes a transparent electrode (510) and a high conductivity rib (550). The structure (500) provides top side light output and a low line resistance, and enables a high resolution display. The structure permits a display to be built on top of a silicon driver chip for active matrix addressing.